

General Description

The ZM060N08HP combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

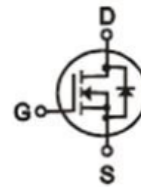
Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

Application

- SMPS 2nd Synchronous Rectifier
- Switching application
- BLDC Motor driver

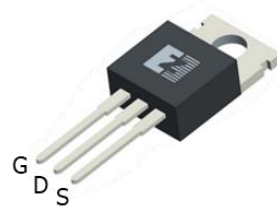
Product Summary



$$V_{DS} = 80V$$

$$R_{DS(ON)} = 6.0m\Omega$$

$$I_D = 80A$$



TO-220

Ordering Information:

Part NO.	ZM060N08HP
Marking	ZM060N08H
Packing Information	Bulk Tube
Basic ordering unit (pcs)	1000

Absolute Maximum Ratings ($T_C = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	80	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25^\circ C}$	80	A
	$I_{D@TC=75^\circ C}$	60	A
	$I_{D@TC=100^\circ C}$	50	A
Pulsed Drain Current ^①	I_{DM}	190	A
Total Power Dissipation($TC=25^\circ C$)	$P_D@TC=25^\circ C$	120	W
Total Power Dissipation($TA=25^\circ C$)	$P_D@TA=25^\circ C$	5	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$
Single Pulse Avalanche Energy@ $L=0.5mH$	E_{AS}	320	mJ
Avalanche Current@ $L=0.5mH$	I_{AS}	36	A

•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	1	$^{\circ}C/W$
Thermal resistance, junction - ambient	R_{thJA}	-	-	25	$^{\circ}C/W$
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	$^{\circ}C$

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	80			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	2		4	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=80V, V_{GS}=0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=16A$		6	8	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=25V, I_D=8A$		28		S
Source-drain voltage	V_{SD}	$I_S=16A$			1.28	V

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=25V$ $f = 1MHz$	-	5600	-	pF
Output capacitance	C_{oss}		-	530	-	
Reverse transfer capacitance	C_{rss}		-	420	-	

•Gate Charge characteristics($T_a = 25^{\circ}C$)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q_g	$V_{DD} = 30V$	-	108	-	nC
Gate - Source charge	Q_{gs}	$I_D = 25A$	-	24	-	
Gate - Drain charge	Q_{gd}	$V_{GS} = 10V$	-	22	-	

Note: ① Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$;

Fig.1 Gate-Charge Characteristics

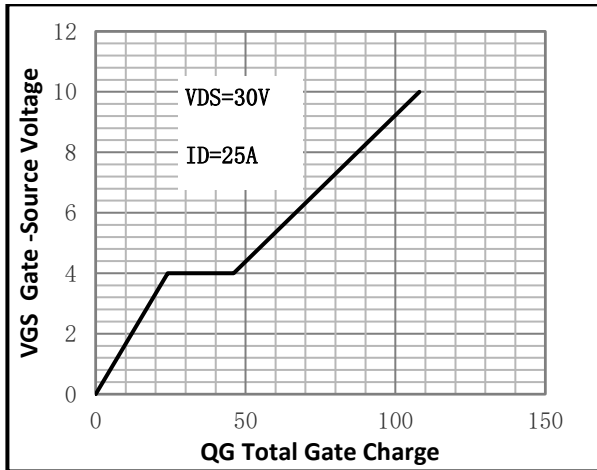


Fig.2 Capacitance Characteristics

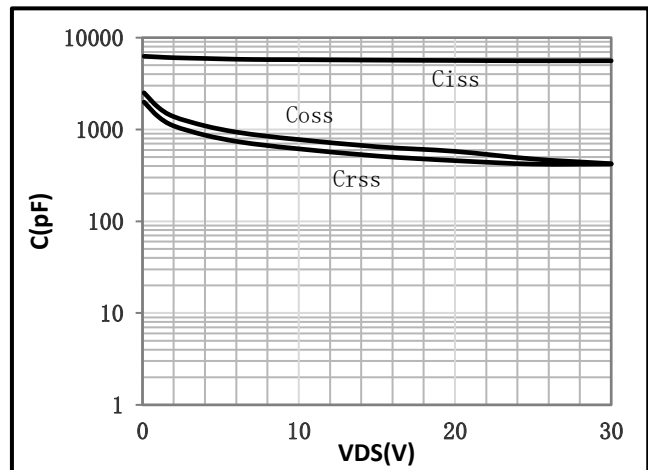


Fig.3 Power Dissipation

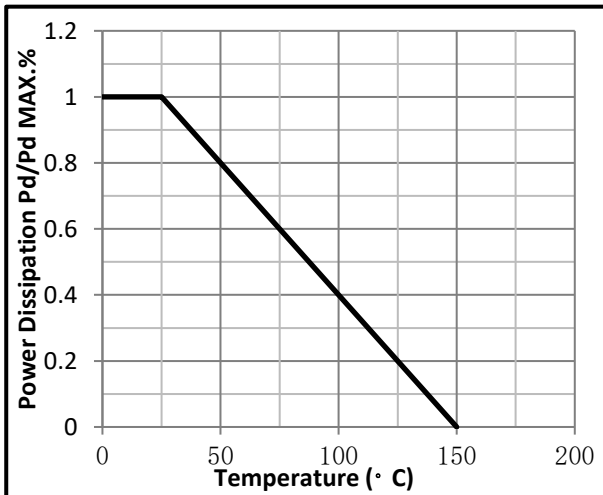


Fig.4 Typical output Characteristics

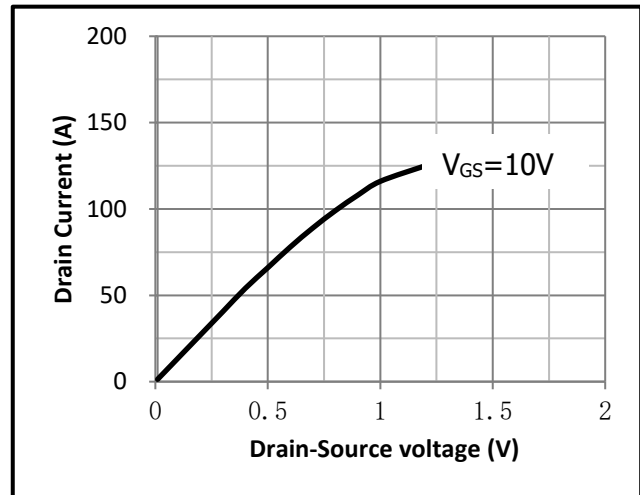


Fig.5 Threshold Voltage V.S Junction Temperature

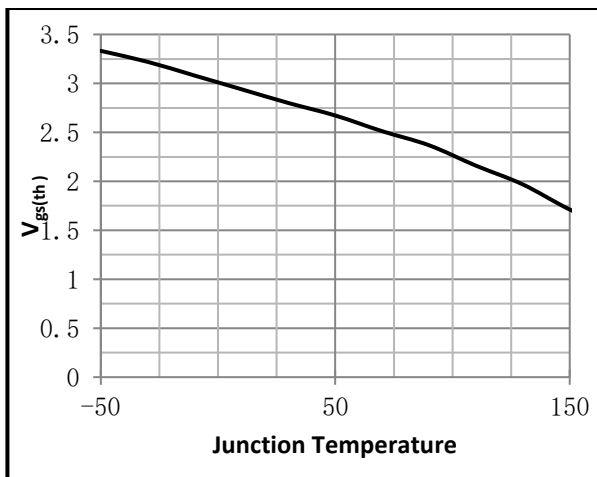


Fig.6 Resistance V.S Drain Current

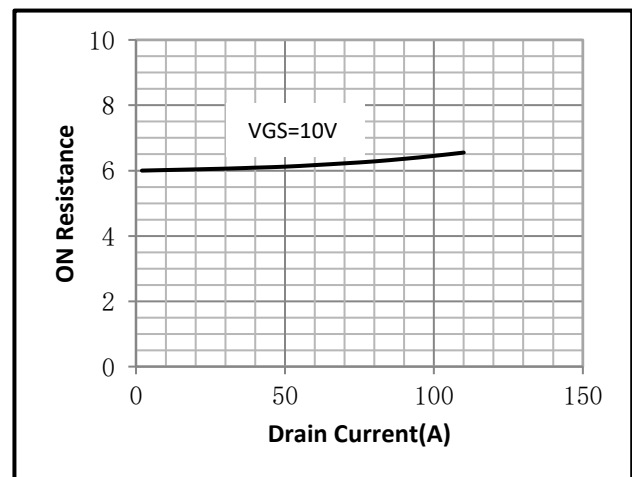


Fig.7 On-Resistance VS Gate Source Voltage

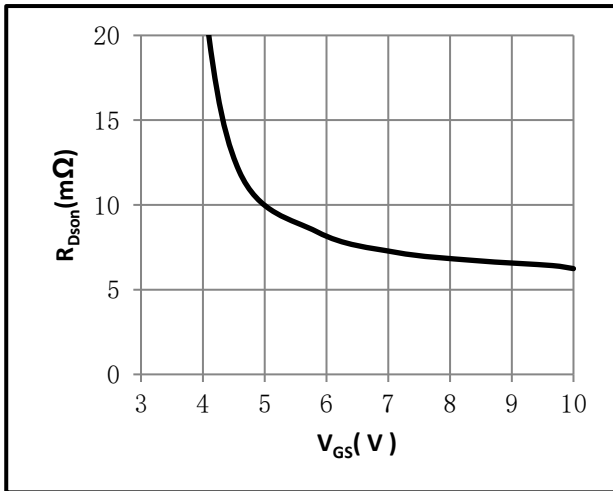


Fig.8 On-Resistance V.S Junction Temperature

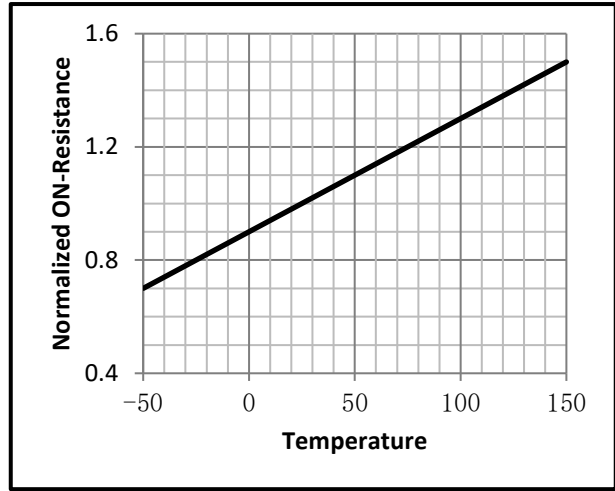


Fig.9 Gate Charge Measurement Circuit

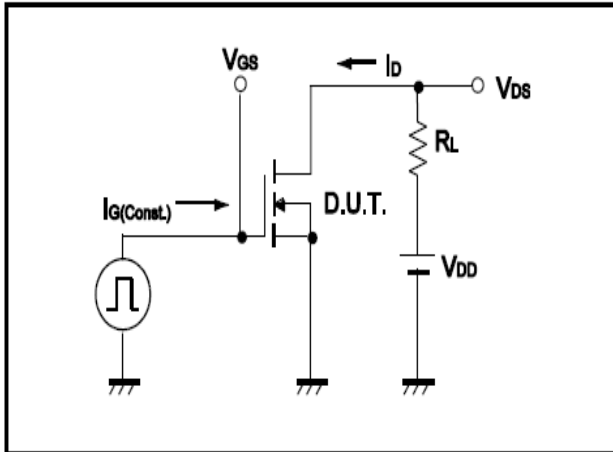


Fig.10 Gate Charge Waveform

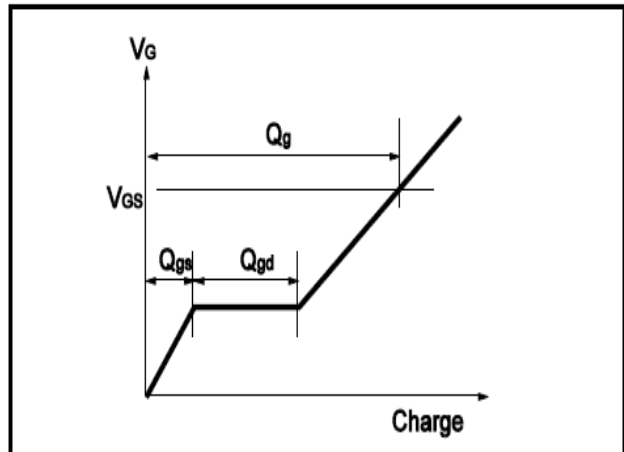


Fig.11 Switching Time Measurement Circuit

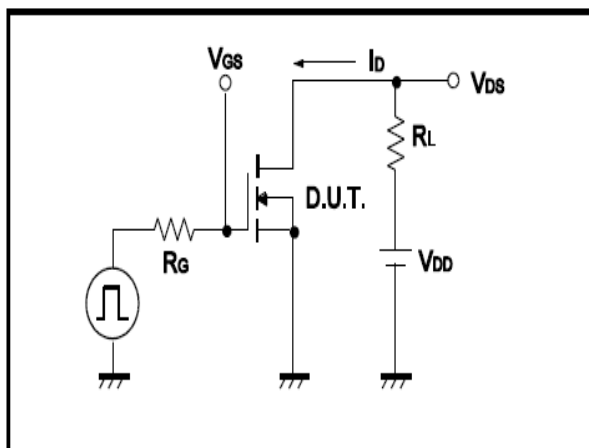
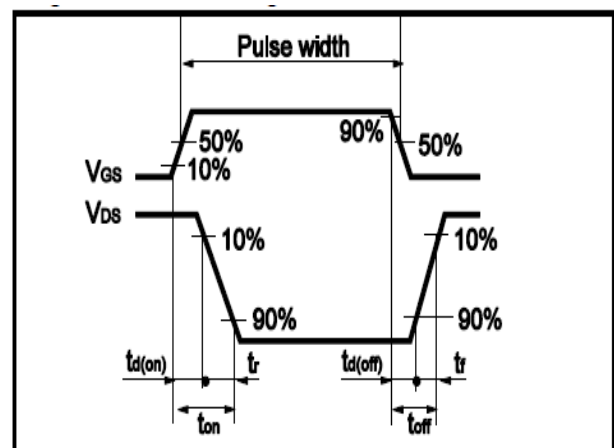


Fig.12 Switching Time Waveform



•Dimensions (TO-220)

Unit: mm

SYMBOL	min	nom	max	SYMBOL	min	nom	max
A	4.00		4.80	E	9.90		10.70
B	1.20		1.50	e		2.54	
B1	1.00		1.40	F	1.10		1.45
b1	0.65		1.00	L	12.50		14.50
c	0.35		0.75	L1	3.00	3.50	4.00
D	15.00		16.50	Q	2.50		3.00
D1	5.90		6.90	Q1	2.00		3.00
				ΦP	3.60		3.90

